

BAS21TW-Q1

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BAS21TW-Q1

**200mA Surface Mount
Switching Diode Array 250V**

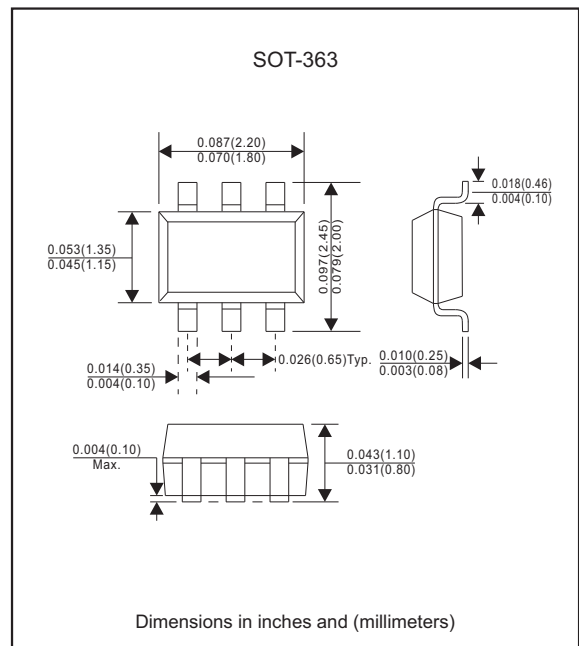
Features

- Fast speed switching
- For general purpose switching application
- High conductance
- Easily connected as full wave bridge
- Silicon epitaxial planar chip
- Lead-free parts meet RoHS requirements
- Qualified to AEC-Q101 standards for high reliability
- Suffix "-H" indicates Halogen-free part, ex. BAS21TW-Q1-H

Mechanical data

- Epoxy: UL94-V0 rated flame retardant
- Case : Molded plastic, SOT-363
- Terminals : Solder plated, solderable per MIL-STD-750, Method 2026
- Mounting Position : Any
- Weight : Approximated 0.006 gram

Package outline



Maximum ratings (AT $T_A=25^{\circ}\text{C}$ unless otherwise noted)

PARAMETER	Symbol	Value	UNIT
Non-repetitive peak reverse voltage	V_{RM}	250	V
Peak repetitive reverse voltage DC blocking voltage	V_{RRM} V_R	250	V
RMS reverse voltage	$V_{R(RMS)}$	177	V
Average rectified output current (Note 1, 3)	I_O	200	mA
Forward continuous current (Note 1)	I_{FM}	400	mA
Non-repetitive peak forward surge current	I_{FSM}	2.5 0.5	A
Thermal resistance junction to ambient (Note 1, 3)	$R_{\theta JA}$	556	$^{\circ}\text{C/W}$
Power dissipation (Note 1)	P_D	225	mW
Operating junction temperature range	T_J	+150	$^{\circ}\text{C}$
Storage temperature range	T_{STG}	-65 to +150	$^{\circ}\text{C}$

Electrical characteristics (AT $T_A=25^{\circ}\text{C}$ unless otherwise noted)

PARAMETER	Symbol	Min.	Max.	UNIT
Reverse breakdown voltage	$V_{(BR)}$	250		V
Forward voltage (Note 2)	V_F		1000 1250	mV
Reverse leakage current (Note 2)	I_R		1.0	μA
Diode capacitance, $V_R = 0\text{V}$, $f = 1.0\text{MHz}$	C_D		5.0	pF
Reverse recovery time ($I_F = I_R = 10\text{mA}$, $I_{rr} = 0.1 \times I_R$, $R_L = 100\Omega$)	t_{rr}		50	ns

Notes1. Device mounted on FR-4 PC board with recommended pad layout.
2. Short duration test pulse used to minimize self-heating effect.
3. One or more diodes loaded.

Rating and characteristic curves for each diode (BAS21TW-Q1)

Fig.1 FORWARD CHARACTERISTICS

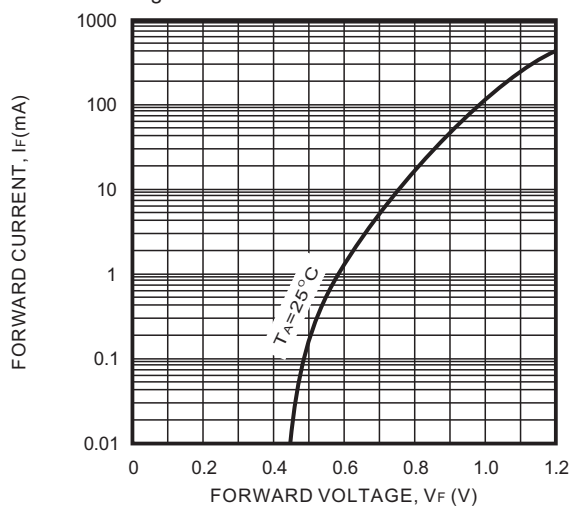


Fig.2 REVERSE CHARACTERISTICS

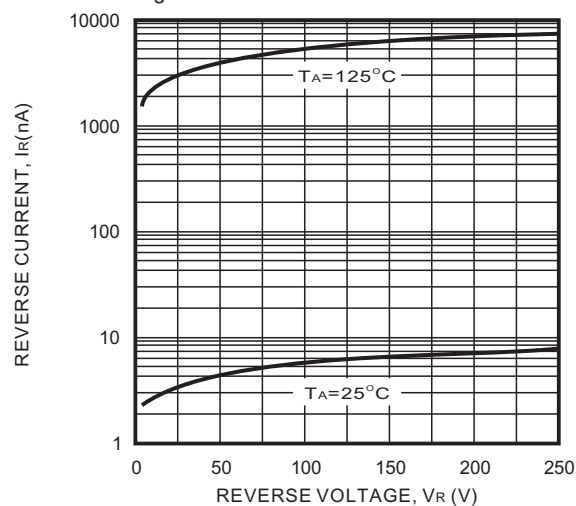


Fig.3 CAPACITANCE CHARACTERISTICS

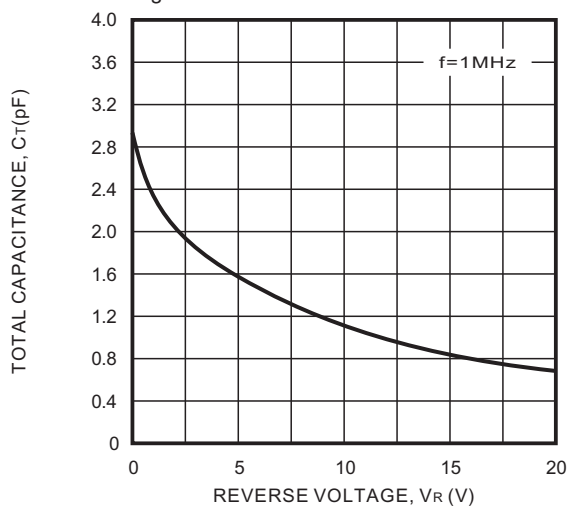
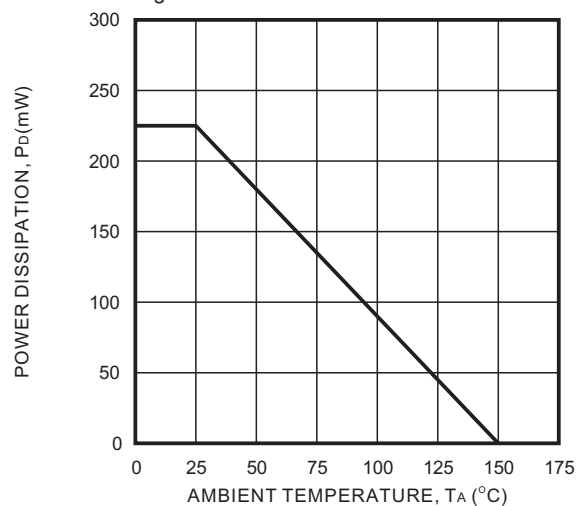
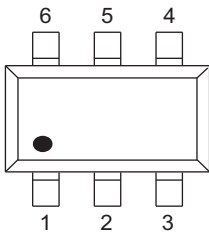
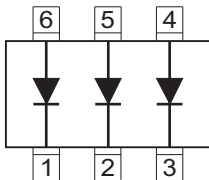


Fig.4 POWER DERATING CURVE



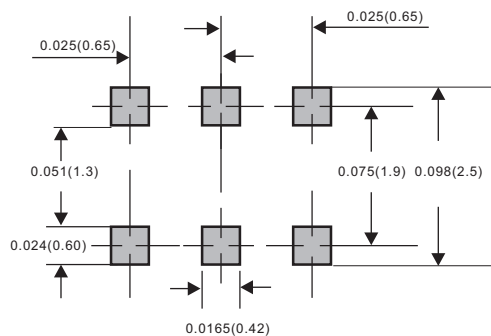
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Pinning information

Type number	Simplified outline	Marking code	Symbol
BAS21TW-Q1		XJK	

Suggested solder pad layout

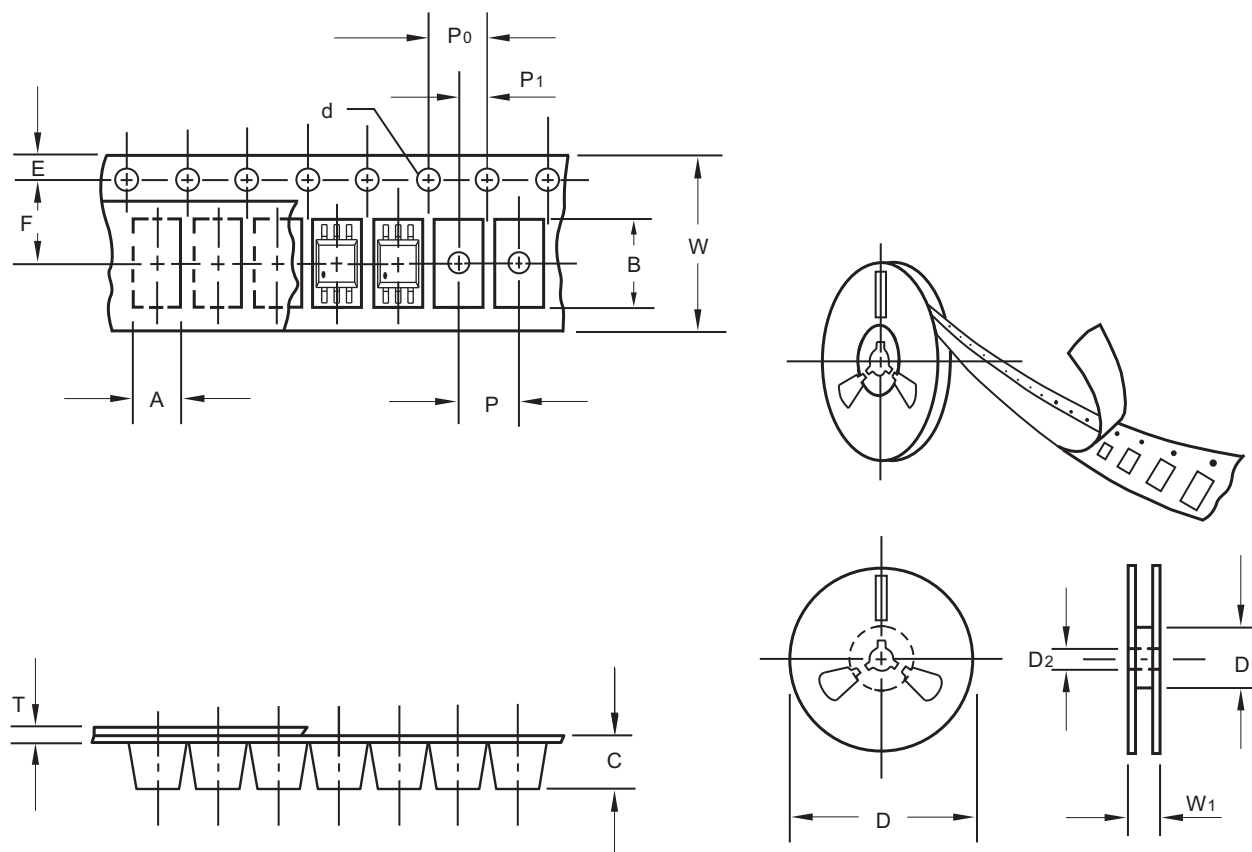
SOT-363



Dimensions in inches and (millimeters)

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Packing information



unit:mm

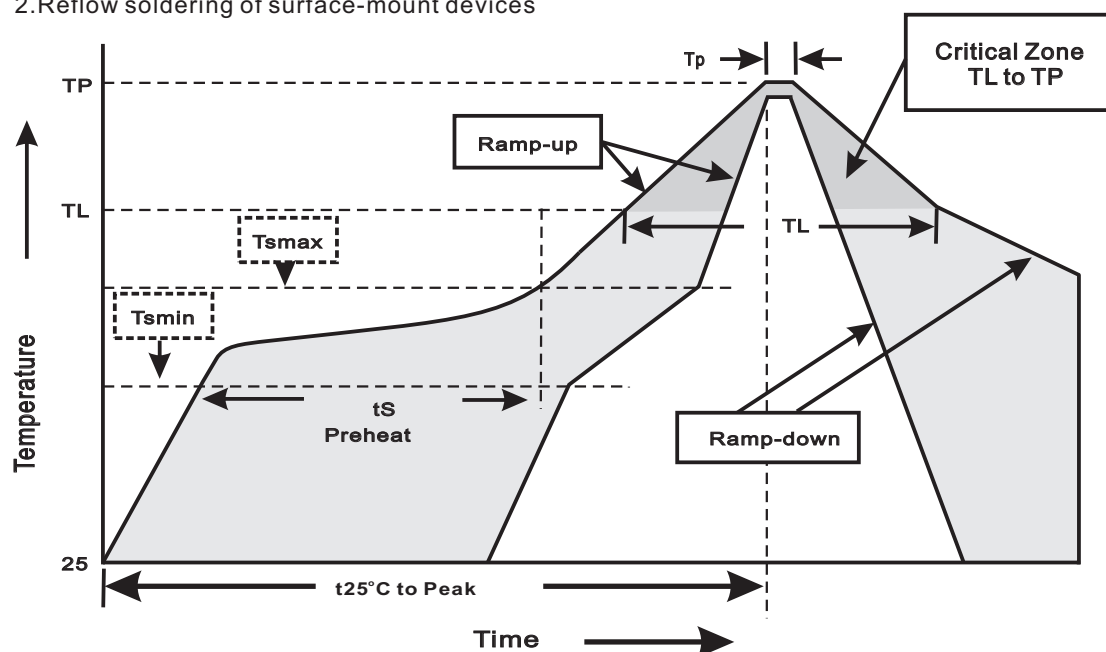
Item	Symbol	Tolerance	SOT-363
Carrier width	A	0.1	2.25
Carrier length	B	0.1	2.55
Carrier depth	C	0.1	1.20
Sprocket hole	d	0.1	1.50
13" Reel outside diameter	D	2.0	-
13" Reel inner diameter	D1	min	-
7" Reel outside diameter	D	2.0	178.00
7" Reel inner diameter	D1	min	54.40
Feed hole diameter	D2	0.5	13.00
Sprocket hole position	E	0.1	1.75
Punch hole position	F	0.1	3.50
Punch hole pitch	P	0.1	4.00
Sprocket hole pitch	P0	0.1	4.00
Embossment center	P1	0.1	2.00
Overall tape thickness	T	0.1	0.23
Tape width	W	0.3	8.00
Reel width	W1	1.0	11.40

Note: Devices are packed in accordance with EIA standard RS-481-A and specifications listed above.

Reel packing

PACKAGE	REEL SIZE	REEL (pcs)	COMPONENT SPACING (m/m)	BOX (pcs)	INNER BOX (m/m)	REEL DIA, (m/m)	CARTON SIZE (m/m)	CARTON (pcs)	APPROX. GROSS WEIGHT (kg)
SOT-363	7"	3,000	4.0	30,000	183*123*183	178	382*257*387	240,000	9.50

2.Reflow soldering of surface-mount devices



Profile Feature	Soldering Condition
Average ramp-up rate(T_L to T_P)	$<3^{\circ}\text{C}/\text{sec}$
Preheat -Temperature Min(T_{min}) -Temperature Max(T_{max}) -Time(min to max)(t_s)	150°C 200°C $60\sim 120\text{sec}$
T_{max} to T_L -Ramp-upRate	$<3^{\circ}\text{C}/\text{sec}$
Time maintained above: -Temperature(T_L) -Time(t_L)	217°C $60\sim 260\text{sec}$
Peak Temperature(T_P)	$255^{\circ}\text{C}-0/+5^{\circ}\text{C}$
Time within 5°C of actual Peak Temperature(t_P)	$10\sim 30\text{sec}$
Ramp-down Rate	$<6^{\circ}\text{C}/\text{sec}$
Time 25°C to Peak Temperature	$<6\text{minutes}$

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High reliability test capabilities

Item Test	Conditions	Reference
1. MSL Preconditioning	24hr bake@125°C+168hrs@85°C /85%RH+3xIR@260°C+1flux immersion+alcohol+DI H2O rinse	JESD22-A113
2. Operation Life	Ta=25°C, Rated Current (Io=Io max.)Test Duration:1000hrs	MIL-STD-750E METHOD 1027.3
3. High Temperature Reverse Bias	80% Rated VR (Tj=Tj max.)Test Duration:1000hrs	JESD22-A108
4. High Temperature Storage Life	Ta= 125°C Test Duration: 1000hrs	JESD22 A-103
5. Temperature Cycle	-55°C (15min) to 150°C (15min)Test Cycles: 1000cycles	JESD22 A-104
6. Autoclave	P=2atm Ta=121°C RH=100% Test Duration:96hrs	JESD22 A-102
7. Intermittent Operational Life	Ta=25°C,On/Io Max. 2min, Off/2min, Test Cycles:15000cycles	MIL-STD-750E METHOD 1037
8. Solderability	245±5°C for 5sec	J-STD-002
9. Moisture Resistance	Ta=85°C/85% Relative humidity Test Duration:1000hrs	MIL-STD-750E METHOD 1021.2
10. Resistance To Solder Heat	260±5°C for 10sec	JESD22 B-106
11. High Temperature High Humidity Reverse Bias	Ta=85°C, 85%RH, with device reverse biased at 80% of rated breakdown voltage up to a maximum of 100V or limit of chamber Test Duration:1000hrs	JESD22-A101